

First Named Inventor	Zhongze Wang	<p style="text-align: center;"><b>INFORMATION DISCLOSURE STATEMENT</b></p>
Serial No.	Unknown	
Filing Date	Filed herewith	
Group Art Unit	Unknown	
Examiner Name	Unknown	
Confirmation No.	Unknown	
Attorney Docket No.	400.147US02	
Title: FET HAVING EPITAXIAL SILICON GROWTH		

Mail Stop: Patent Application  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

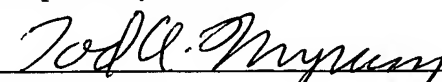
In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

Further pursuant to MPEP §609, because all of the references listed on the attached Form 1449 have been previously submitted and made of record in the parent application, U.S. Patent Application 10/073,723, filed February 11, 2002, copies of the references previously made of record in the parent application are not submitted herewith.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at the number listed below.

Respectfully submitted,

Date: 01-15-2004

  
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T – 612/312-2200  
F – 612/312-2250

First Named Inventor	Wang Zhongze	<p align="center"><b>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b></p>
Serial No.	Unknown	
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Title: FET HAVING EPITAXIAL SILICON GROWTH		Sheet 1 of 1

U.S. Patent References				
Examiner Initials	Document No.	Publication Date (mm/dd/yy)	Name	Filing Date (mm/dd/yy)
	09/713,844	Unknown	Abbott ete al.	11/15/00
	5,908,313	06/01/99	Chau et al.	12/31/96
	6,156,589	12/05/00	Noble	09/03/98
	6,180,494 B1	01/30/01	Manning	03/11/99
	6,274,913 B1	08/14/01	Brigham et al.	10/05/98
	6,300,219 B1	10/09/01	Doan et al.	08/30/99
	6,358,798 B1	03/19/02	Chen	09/06/00
	6,388,294 B1	05/14/02	Radens et al.	11/22/00
	6,391,726 B1	05/21/02	Manning	06/29/00

Foreign Patent References					
Examiner Initials	Foreign Patent		Name	Publication Date	Translation
	Country	No.			

Other References	
Examiner Initials	Author, Title, Date, Pages, etc.
	S. Wolf et al, "Silicon Epitaxial Film Growth," <u>Silicon Processing for the VLSI Era</u> , Vol. 1, 1986, pp. 124-160.

Examiner Signature		Date Considered	
<p>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>			